

Title (en)

Temperature stable current source

Title (de)

Temperaturstabilisierte Stromquelle

Title (fr)

Source de courant stable en température

Publication

**EP 0687967 B1 19980408 (FR)**

Application

**EP 95401363 A 19950612**

Priority

FR 9407407 A 19940613

Abstract (en)

[origin: FR2721119A1] The current source includes first and second MOS transistors (N0,N1) supplied by a current mirror (1) which have their sources connected to earth (Vss), in order to make the current source insensitive to temperature. The drain (a) and the grid (b) of the second transistor (N1) are connected via a resistance (R). The transfer coefficient of the transistors (N0,N1) is equal to the coefficient (beta) of the current mirror (1), and the transistors (N0,N1) are doped so that the threshold of the second transistor (N1) is greater than that of the first transistor (N0).

IPC 1-7

**G05F 3/30**; **G05F 3/26**

IPC 8 full level

**G05F 3/24** (2006.01); **G05F 3/26** (2006.01); **G05F 3/30** (2006.01); **H03F 3/343** (2006.01); **H03F 3/347** (2006.01)

CPC (source: EP US)

**G05F 3/262** (2013.01 - EP US); **G05F 3/30** (2013.01 - EP US); **Y10S 323/907** (2013.01 - EP)

Cited by

FR2744262A1; EP0788047A1; US5903141A; US8085029B2; WO2008121123A1

Designated contracting state (EPC)

DE FR GB IT

DOCDB simple family (publication)

**EP 0687967 A1 19951220**; **EP 0687967 B1 19980408**; DE 69501980 D1 19980514; DE 69501980 T2 19980806; FR 2721119 A1 19951215; FR 2721119 B1 19960719; JP 2684600 B2 19971203; JP H08123565 A 19960517; US 5644216 A 19970701

DOCDB simple family (application)

**EP 95401363 A 19950612**; DE 69501980 T 19950612; FR 9407407 A 19940613; JP 17038995 A 19950613; US 45492695 A 19950531